

March 2013

FDP047N10

N-Channel PowerTrench[®] MOSFET 100 V, 164 A, 4.7 m Ω

Description

- $R_{DS(on)}$ = 3.9 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 75 A
- · Fast Switching Speed
- · Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{\text{DS}(\text{on})}$
- · High Power and Current Handing Capability
- · RoHS Compliant

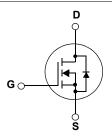
General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor $^{\text{\tiny B}}$'s advance PowerTrench $^{\text{\tiny B}}$ process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- · Battery Protection Circuit
- · Motor Drives and Uninterruptible Power Supplies
- · Micro Solar Inverter





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted*

Symbol		Parameter		FDP047N10	Unit
V_{DSS}	Drain to Source Voltage			100	V
V_{GSS}	Gate to Source Voltage			±20	V
	Drain Current - Cor	ntinuous (T _C = 25°C, Silicon Limited)		164*	Α
I_D	- Continuous (T _C = 100°C, Silicon Limited)			116*	Α
	- Coi	ntinuous (T _C = 25°C, Package Limited	d)	120	Α
I _{DM}	Drain Current	- Pulsed (f	Note 1)	656*	Α
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		Note 2)	1153	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		Note 3)	6.0	V/ns
D	Dower Dissipation	$(T_C = 25^{\circ}C)$		375	W
P_{D}	Power Dissipation - Derate above 25°C			2.5	W/°C
T _J , T _{STG}	Operating and Storage Tempera	ture Range		-55 to +175	°C
T _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			300	°C

^{*}Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 120A.

Thermal Characteristics

Symbol	Parameter	FDP047N10	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.4	
$R_{\theta CS}$	Thermal Resistance, Case to Sink Typ.	0.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP047N10	FDP047N10	TO-220	-	-	50

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter Test Conditions		Min.	Тур.	Max.	Unit
Off Charac	eteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A$, $V_{GS} = 0V$, $T_J = 25^{\circ}C$	100	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C	-	0.1	-	V/°C
1	Zero Gate Voltage Drain Current	V _{DS} = 100V, V _{GS} = 0V	-	-	1	^
IDSS	Zero Gate voltage Drain Current	$V_{DS} = 100V, V_{GS} = 0V, T_{C} = 150^{\circ}C$	-	-	500	μА
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	2.5	3.5	4.5	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10V, I _D = 75A	-	3.9	4.7	mΩ
9 _{FS}	Forward Transconductance	$V_{DS} = 10V, I_{D} = 75A$	ı	170	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V = 25V V = 0V	-	11500	15265	pF
C _{oss}	Output Capacitance	V _{DS} = 25V, V _{GS} = 0V f = 1MHz	-	1120	1500	pF
C _{rss}	Reverse Transfer Capacitance	1 – 111112	-	455	680	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay Time			-	174	358	ns
t _r	Turn-On Rise Time	V _{DD} = 50V, I _D = 75A	$V_{DD} = 50V, I_{D} = 75A$ $V_{GS} = 10V, R_{GEN} = 25\Omega$		386	782	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10V, R_{GEN} = 25 Ω			344	698	ns
t _f	Turn-Off Fall Time		(Note 4)	-	244	499	ns
Q _{g(tot)}	Total Gate Charge at 10V	Vpc = 80V lp = 75A		-	160	210	nC
Q_{gs}	Gate to Source Gate Charge	$V_{DS} = 80V, I_D = 75A$ $V_{GS} = 10V$		-	56	-	nC
Q _{gd}	Gate to Drain "Miller" Charge		(Note 4)	-	36	-	nC

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	164*	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	656	Α
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _{SD} = 75A	-	-	1.25	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _{SD} = 75A	-	88	-	ns
Qrr	Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	-	245	-	nC

Notes:

- Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L = 0.41mH, I $_{AS}$ = 75A, V $_{DD}$ = 50V, R $_{G}$ = 25 Ω , Starting T $_{J}$ = 25°C
- 3. I $_{SD} \le 75$ A, di/dt ≤ 200 A/ μ s, $V_{DD} \le BV_{DSS}$, Starting T $_{J}$ = 25°C
- 4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

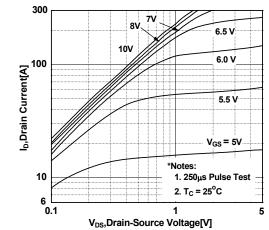


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

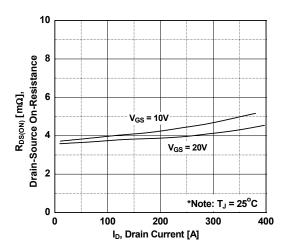


Figure 5. Capacitance Characteristics

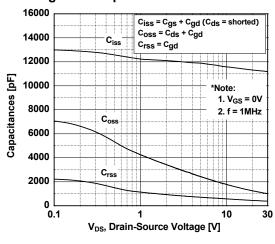


Figure 2. Transfer Characteristics

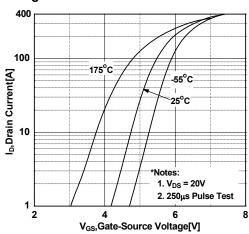


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

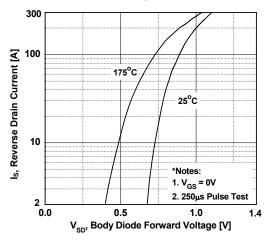
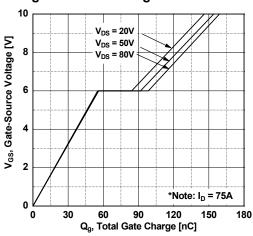


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

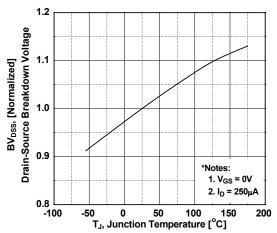


Figure 8. On-Resistance Variation vs. Temperature

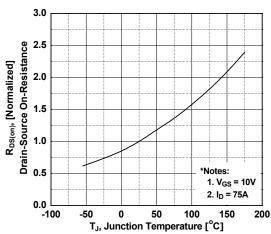


Figure 9. Maximum Safe Operating Area

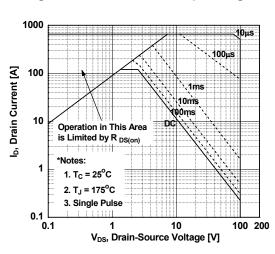


Figure 10. Maximum Drain Current vs. Case Temperature

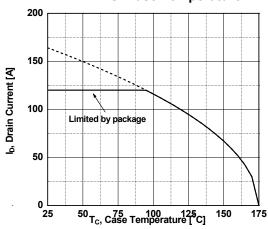
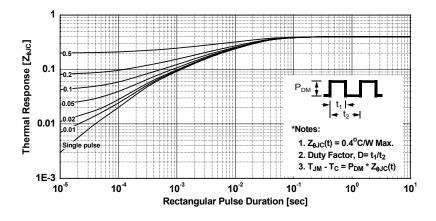
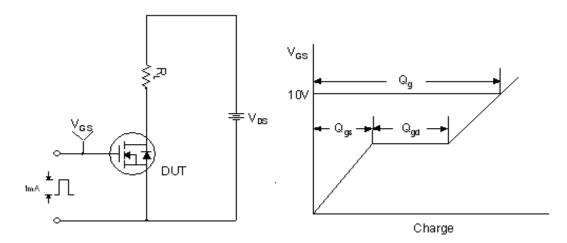


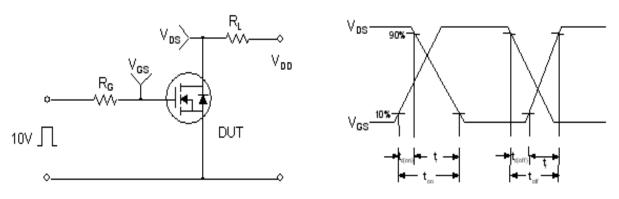
Figure 11. Transient Thermal Response Curve



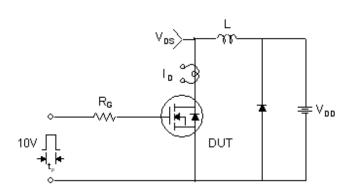
Gate Charge Test Circuit & Waveform

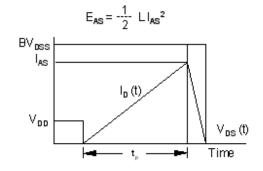


Resistive Switching Test Circuit & Waveforms

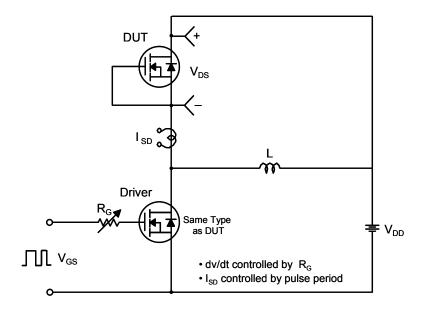


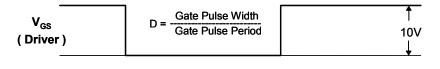
Unclamped Inductive Switching Test Circuit & Waveforms

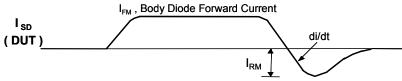




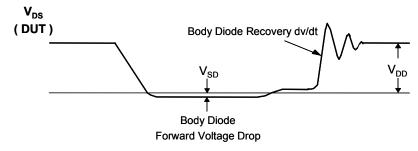
Peak Diode Recovery dv/dt Test Circuit & Waveforms





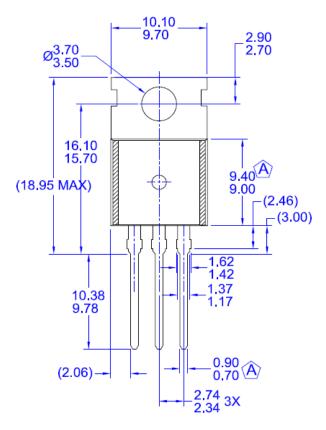


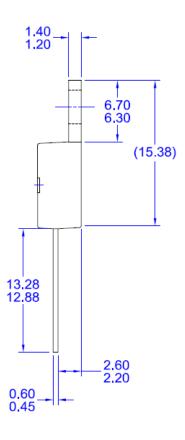
Body Diode Reverse Current

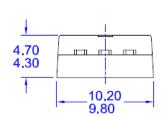


Mechanical Dimensions

TO-220Y03







NOTES:

- (A) CONFORMS TO JEDEC TO-220 VARIATION AB EXCEPT WHERE NOTED
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- D) DRAWING FILE/REVISION: MKT-TO220Y03REV1

Dimensions in Millimeters





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